# Philipp Ebert

List of Publications by Year
in descending order



| 130 | 3,194 | 126907 | 189892 |
|---|---|---|---|
| papers | citations | 33 | 50 |
| | | h-index | g-index |

| 131 | 131 | 131 | 2112 |
|---|---|---|---|
| all docs | docs citations | times ranked | citing authors |

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | Nano-scale properties of defects in compound semiconductor surfaces. Surface Science Reports, 1999, 33, 121-303. | 7.2 | 165 |
| 2 | Evidence for a Cluster-Based Structure of AlPdMn Single Quasicrystals. Physical Review Letters, 1996, 77, 3827-3830. | 7.8 | 161 |
| 3 | Quasicrystalline Epitaxial Single Element Monolayers on Icosahedral Al-Pd-Mn and Decagonal Al-Ni-Co Quasicrystal Surfaces. Physical Review Letters, 2002, 89, 156104. | 7.8 | 124 |
| 4 | Microscopic identification of the compensation mechanisms in Si-doped GaAs. Physical Review B, 1996, 54, 10288-10291. | 3.2 | 115 |
| 5 | Charge state dependent structural relaxation around anion vacancies on InP(110) and GaP(110) surfaces. Physical Review Letters, 1994, 72, 840-843. | 7.8 | 79 |
| 6 | Contribution of Surface Resonances to Scanning Tunneling Microscopy Images: (110) Surfaces of III-V Semiconductors. Physical Review Letters, 1996, 77, 2997-3000. | 7.8 | 78 |
| 7 | Comparison betweenab initiotheory and scanning tunneling microscopy for (110) surfaces of III-V semiconductors. Physical Review B, 1998, 58, 7799-7815. | 3.2 | 71 |
| 8 | Identification and Quantification of Defects in Highly Si-Doped GaAs by Positron Annihilation and Scanning Tunneling Microscopy. Physical Review Letters, 1997, 78, 3334-3337. | 7.8 | 66 |
| 9 | Direct Determination of the Interaction between Vacancies on InP(110) Surfaces. Physical Review Letters, 1996, 76, 2089-2092. | 7.8 | 64 |
| 10 | Surface structures of cleaved icosahedral Al-Pd-Mn single quasicrystals after heat treatment. Physical Review B, 1998, 57, 2821-2825. | 3.2 | 60 |
| 11 | Direct Evidence for Shallow Acceptor States with Nonspherical Symmetry in GaAs. Physical Review Letters, 2005, 94, 026407. | 7.8 | 60 |
| 12 | Thermal formation of Zn-dopant-vacancy defect complexes on InP(110) surfaces. Physical Review B, 1996, 53, 4580-4590. | 3.2 | 59 |
| 13 | Scanning-tunneling-microscope tip-induced migration of vacancies on GaP(110). Physical Review Letters, 1993, 70, 1437-1440. | 7.8 | 58 |
| 14 | Surface states and origin of the Fermi level pinning on nonpolar GaN(11Â¯00) surfaces. Applied Physics Letters, 2008, 93, 192110. | 3.3 | 57 |
| 15 | Formation of anion vacancies by Langmuir evaporation from InP and GaAs (110) surfaces at low temperatures. Physical Review B, 1995, 51, 9696-9701. | 3.2 | 56 |
| 16 | Building Pb Nanomesas with Atomic-Layer Precision. Physical Review Letters, 2004, 92, 106104. | 7.8 | 52 |
| 17 | Hidden surface states at non-polar GaN (101Â¯) facets: Intrinsic pinning of nanowires. Applied Physics Letters, 2013, 103, . | 3.3 | 45 |
| 18 | Enhanced surface metallic density of states in icosahedral quasicrystals. Physical Review B, 1998, 58, 734-738. | 3.2 | 44 |

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| 19 | Symmetric Versus Nonsymmetric Structure of the Phosphorus Vacancy on InP(110). Physical Review Letters, 2000, 84, 5816-5819. | 7.8 | 44 |
| 20 | Atomic-scale structure of the fivefold surface of an AlPdMn quasicrystal: A quantitative x-ray photoelectron diffraction analysis. Physical Review B, 2004, 69, . | 3.2 | 43 |
| 21 | Direct measurement of the band gap and Fermi level position at InN(112Â¯). Applied Physics Letters, 2011, 98, . | 3.3 | 42 |
| 22 | Importance of Many-Body Effects in the Clustering of Charged Zn Dopant Atoms in GaAs. Physical Review Letters, 1999, 83, 757-760. | 7.8 | 41 |
| 23 | Quantitative Determination of the Metastability of Flat Ag Overlayers on GaAs(110). Physical Review Letters, 2001, 88, 016102. | 7.8 | 41 |
| 24 | Determination of the Gibbs free energy of formation of Ga vacancies in GaAs by positron annihilation. Physical Review B, 2003, 67, . | 3.2 | 39 |
| 25 | Importance of carrier dynamics and conservation of momentum in atom-selective STM imaging and band gap determination of GaAs(110). Physical Review B, 2003, 67, . | 3.2 | 38 |
| 26 | Photodriven Dipole Reordering: Key to Carrier Separation in Metalorganic Halide Perovskites. ACS Nano, 2019, 13, 4402-4409. | 14.6 | 38 |
| 27 | Phosphorus vacancies and adatoms on GaP(110) surfaces studied by scanning tunneling microscopy. Ultramicroscopy, 1993, 49, 344-353. | 1.9 | 37 |
| 28 | Evolution of the composition and structure of cleaved and heat-treated icosahedral Al-Pd-Mn quasicrystal surfaces. Physical Review B, 1999, 60, 874-880. | 3.2 | 37 |
| 29 | Atomic structure of point defects in compound semiconductor surfaces. Current Opinion in Solid State and Materials Science, 2001, 5, 211-250. | 11.5 | 36 |
| 30 | Direct measurement and analysis of the conduction band density of states in diluted<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>GaAs</mml:mtext></mml:mrow><mml:mrow><mml:mn>1</mml:mn></mml:mrow></mml:msub></mml:mrow></mml:math>. Physical Review B, 2010, 82, . | 3.2 | 35 |
| 31 | Oscillating contrast in room-temperature scanning tunneling microscope images of localized charges in IIIâ€“V semiconductor cleavage surfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 2825. | 1.6 | 34 |
| 32 | Coulomb Energy Determination of a Single Si Dangling Bond. Physical Review Letters, 2010, 105, 226404. | 7.8 | 34 |
| 33 | Electronic structure of wurtzite II-VI compound semiconductor cleavage surfaces studied by scanning tunneling microscopy. Physical Review B, 1997, 56, 12321-12326. | 3.2 | 33 |
| 34 | Electronic properties of dislocations in GaN investigated by scanning tunneling microscopy. Applied Physics Letters, 2009, 94, 062104. | 3.3 | 33 |
| 35 | Tuning Band Gap and Work Function Modulations in Monolayer hBN/Cu(111) Heterostructures with MoirÃ© Patterns. ACS Nano, 2018, 12, 9355-9362. | 14.6 | 33 |
| 36 | Charged steps on III-V compound semiconductor surfaces. Physical Review B, 1996, 53, 10894-10897. | 3.2 | 30 |

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| 37 | Temperature dependent vacancy concentrations on InP(110) surfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1995, 13, 1714-1718. | 2.1 | 28 |
| 38 | Band offsets at zincblende-wurtzite GaAs nanowire sidewall surfaces. Applied Physics Letters, 2013, 103, . | 3.3 | 28 |
| 39 | The electronic structure of the InP(110) surface studied by scanning tunneling microscopy and spectroscopy. Surface Science, 1992, 271, 587-595. | 1.9 | 27 |
| 40 | A STM study of the InP (110) surface. Ultramicroscopy, 1992, 42-44, 871-877. | 1.9 | 27 |
| 41 | Scanning tunneling microscopy and spectroscopy of semi-insulating GaAs. Physical Review B, 2002, 65, . | 3.2 | 27 |
| 42 | Physics of imagingpâ^'njunctions by scanning tunneling microscopy and spectroscopy. Physical Review B, 2003, 67, . | 3.2 | 27 |
| 43 | Nanoscale dopant-induced dots and potential fluctuations in GaAs. Applied Physics Letters, 2003, 82, 2700-2702. | 3.3 | 27 |
| 44 | Direct observation of electrical charges at dislocations in GaAs by cross-sectional scanning tunneling microscopy. Applied Physics Letters, 2001, 78, 480-482. | 3.3 | 26 |
| 45 | Defects in III-V semiconductor surfaces. Applied Physics A: Materials Science and Processing, 2002, 75, 101-112. | 2.3 | 26 |
| 46 | Compensation mechanisms in low-temperature-grown Ga1â^'xMnxAs investigated by scanning tunneling spectroscopy. Applied Physics Letters, 2003, 82, 712-714. | 3.3 | 26 |
| 47 | Scanning tunneling spectroscopy of quantum well and surface states of thin Ag films grown on GaAs(110). Physical Review B, 2001, 64, . | 3.2 | 24 |
| 48 | Determination of the charge carrier compensation mechanism in Te-doped GaAs by scanning tunneling microscopy. Applied Physics Letters, 2003, 82, 2059-2061. | 3.3 | 24 |
| 49 | Atomic-scale properties of the amphoteric dopant Si in GaAs(110) surfaces. Surface Science, 1998, 415, 285-298. | 1.9 | 23 |
| 50 | Changes of defect and active-dopant concentrations induced by annealing of highly Si-doped GaAs. Physical Review B, 1998, 57, 4482-4485. | 3.2 | 23 |
| 51 | Substrate effects on the formation of flat Ag films on (110) surfaces of III-V compound semiconductors. Physical Review B, 1999, 60, 4988-4991. | 3.2 | 23 |
| 52 | Effect of the Si substrate structure on the growth of two-dimensional thin Ag films. Surface Science, 2002, 518, 63-71. | 1.9 | 23 |
| 53 | Surface structure of Al-Pd-Mn quasicrystals:â€ƒExistence of supersaturated bulk vacancy concentrations. Physical Review B, 2003, 67, . | 3.2 | 22 |
| 54 | Scanning tunneling microscopy on unpinned<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mtext>GaN</mml:mtext><mml:mrow><mml:mo>(</mml:mo><mml:mrow><mml:mn>1</mml:mn> Invisibility of valence-band states. Physical Review B, 2009, 80, . | 3.2 | 22 |

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| 55 | Nonâ€polar groupâ€III nitride semiconductor surfaces. Physica Status Solidi - Rapid Research Letters, 2012, 6, 359-369. | 2.4 | 22 |
| 56 | Growth and electronic structure of alkali-metal adlayers on icosahedralAl70.5Pd21Mn8.5. Physical Review B, 2006, 73, . | 3.2 | 21 |
| 57 | Identification of surface anion antisite defects in (110) surfaces of IIIâ€“V semiconductors. Applied Physics Letters, 2001, 79, 2877-2879. | 3.3 | 20 |
| 58 | Origin of nanoscale potential fluctuations in two-dimensional semiconductors. Applied Physics Letters, 2009, 95, . | 3.3 | 20 |
| 59 | Dislocations, Phason Defects, and Domain Walls in a One-Dimensional Quasiperiodic Superstructure of a Metallic Thin Film. Physical Review Letters, 1999, 83, 3222-3225. | 7.8 | 19 |
| 60 | Quantitative description of photoexcited scanning tunneling spectroscopy and its application to the GaAs(110) surface. Physical Review B, 2015, 91, . | 3.2 | 18 |
| 61 | Three- to two-dimensional transition in electrostatic screening of point charges at semiconductor surfaces studied by scanning tunneling microscopy. Physical Review B, 2009, 80, . | 3.2 | 17 |
| 62 | Structure and electronic spectroscopy of steps on GaAs(110) surfaces. Surface Science, 2012, 606, 28-33. | 1.9 | 17 |
| 63 | Polarity-dependent pinning of a surface state. Physical Review B, 2015, 91, . | 3.2 | 17 |
| 64 | Imaging defects and dopants. Materials Today, 2003, 6, 36-43. | 14.2 | 16 |
| 65 | Core and valence level photoemission and photoabsorption study of icosahedral Alâ€“Pdâ€“Mn quasicrystals. Journal of Physics Condensed Matter, 2006, 18, 435-448. | 1.8 | 16 |
| 66 | Temperature dependent compensation of Znâ€dopant atoms by vacancies in IIIâ€“V semiconductor surfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1996, 14, 1807-1811. | 2.1 | 15 |
| 67 | Direct identification of As vacancies in GaAs using positron annihilation calibrated by scanning tunneling microscopy. Physical Review B, 2001, 63, . | 3.2 | 15 |
| 68 | Steps on CdSe (112Â¯0) and (101Â¯0) cleavage surfaces: Evidence for crack propagation in competing cleavage planes. Physical Review B, 1999, 59, 3000-3007. | 3.2 | 14 |
| 69 | Imaging individual dopant atoms on cleavage surfaces of wurtzite-structure compound semiconductors. Physical Review B, 1999, 59, 2995-2999. | 3.2 | 14 |
| 70 | Stoichiometry changes by selective vacancy formation on (110) surfaces of IIIâ€“V semiconductors: Influence of electronic effects. Journal of Chemical Physics, 2001, 114, 445. | 3.0 | 14 |
| 71 | Quantum size effect induced dilute atomic layers in ultrathin Al films. Physical Review B, 2007, 76, . | 3.2 | 14 |
| 72 | Electronic properties of the Ga vacancy in GaP(110) surfaces determined by scanning tunneling microscopy. Physical Review B, 1998, 58, 1401-1404. | 3.2 | 13 |

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| 73 | Effect of dopant atoms on the roughness of IIIâ€“V semiconductor cleavage surfaces. Applied Physics Letters, 2000, 76, 300-302. | 3.3 | 13 |
| 74 | Structure and composition of cleaved and heat-treated tenfold surfaces of decagonal Alâ€“Niâ€“Co quasicrystals. Surface Science, 2003, 523, 298-306. | 1.9 | 13 |
| 75 | Reverse mass transport during capping of In0.5Ga0.5As/GaAs quantum dots. Applied Physics Letters, 2012, 101, . | 3.3 | 13 |
| 76 | Importance of quantum correction for the quantitative simulation of photoexcited scanning tunneling spectra of semiconductor surfaces. Physical Review B, 2016, 93, . | 3.2 | 13 |
| 77 | Atomically Resolved Electronic States and Correlated Magnetic Order at Termination Engineered Complex Oxide Heterointerfaces. ACS Nano, 2018, 12, 1089-1095. | 14.6 | 13 |
| 78 | Influence of grown-in voids on the structure of cleaved icosahedral Alâ€“Pdâ€“Mn quasicrystal surfaces. Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing, 2000, 294-296, 874-877. | 5.6 | 12 |
| 79 | Effect of charge carriers on the barrier height for vacancy formation on InP(110) surfaces. Applied Physics Letters, 2000, 77, 61-63. | 3.3 | 12 |
| 80 | Electron affinity and surface states of GaN <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>m</mml:mi></mml:math> -plane facets: Implication for electronic self-passivation. Physical Review B, 2018, 97, . | 3.2 | 12 |
| 81 | Influence of growth kinetics and chemical composition on the shape of voids in quasi-crystals. Surface Science, 2002, 519, 33-39. | 1.9 | 11 |
| 82 | Doping modulation in GaN imaged by cross-sectional scanning tunneling microscopy. Applied Physics Letters, 2009, 94, 162110. | 3.3 | 11 |
| 83 | Atomic resolution in tunneling induced light emission from GaAs(110). Applied Physics Letters, 2010, 96, 152107. | 3.3 | 11 |
| 84 | Quantum size effects in the nonmetal to metal transition of two-dimensional Al islands. Physical Review B, 2007, 76, . | 3.2 | 10 |
| 85 | Dopant atom clustering and charge screening induced roughness of electronic interfaces in GaAsp-nmultilayers. Physical Review B, 2002, 65, . | 3.2 | 9 |
| 86 | Nanoscale fluctuations in the distribution of dopant atoms: Dopant-induced dots and roughness of electronic interfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 2018. | 1.6 | 9 |
| 87 | Nonicosahedral Equilibrium Overlayers of Icosahedral Quasicrystals. Physical Review Letters, 2005, 95, 256105. | 7.8 | 9 |
| 88 | Manganese adlayers on i-Alâ€“Pdâ€“Mn quasicrystal: growth and electronic structure. Journal of Physics Condensed Matter, 2009, 21, 405005. | 1.8 | 9 |
| 89 | Cross-sectional scanning tunneling microscopy and spectroscopy of nonpolar GaN(11Â¯00) surfaces. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, C5G11-C5G18. | 1.2 | 9 |
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| 91 | Correction of nonlinear lateral distortions of scanning probe microscopy images. Ultramicroscopy, 2014, 136, 86-90. | 1.9 | 9 |
| 92 | Probing the step structure of buried metal/semiconductor interfaces using quantized electron states: The case of Pb on Si(111) 6Ã—6-Au. Applied Physics Letters, 2002, 81, 2005-2007. | 3.3 | 8 |
| 93 | Evidence of deep traps in overgrown v-shaped defects in epitaxial GaN layers. Applied Physics Letters, 2013, 103, . | 3.3 | 8 |
| 94 | Intrinsic bandgap of cleaved ZnO(112Â¯0) surfaces. Applied Physics Letters, 2013, 102, 021608. | 3.3 | 8 |
| 95 | Intrinsic electronic properties of high-quality wurtzite InN. Physical Review B, 2016, 94, . | 3.2 | 8 |
| 96 | Step smoothing and surface vacancy reactions on InP(110) and GaP(110) observed by scanning tunneling microscopy. Surface Science, 1993, 287-288, 891-895. | 1.9 | 7 |
| 97 | Evidence for a two-step evolution of the surface structure during heat treatment of cleaved icosahedral Alâ€“Pdâ€“Mn single quasicrystals. Surface Science, 1999, 433-435, 312-316. | 1.9 | 7 |
| 98 | Dopant mapping of Be Î´-doped layers in GaAs tailored by counterdoping using scanning tunneling microscopy. Applied Physics Letters, 2012, 101, . | 3.3 | 7 |
| 99 | Lazarevicite-type short-range ordering in ternary III-V nanowires. Physical Review B, 2016, 94, . | 3.2 | 7 |
| 100 | Growing extremely thin bulklike metal film on a semiconductor surface: Monolayer Al(111) on Si(111). Applied Physics Letters, 2007, 91, . | 3.3 | 6 |
| 101 | Quantitative determination of local potential values in inhomogeneously doped semiconductors by scanning tunneling microscopy. Physical Review B, 2011, 84, . | 3.2 | 6 |
| 102 | Probing defect states in polycrystalline GaN grown on Si(111) by sub-bandgap laser-excited scanning tunneling spectroscopy. Journal of Applied Physics, 2017, 121, 015701. | 2.5 | 5 |
| 103 | Fermi-level pinning and intrinsic surface states of Al1â^'xInxN(101Â¯) surfaces. Applied Physics Letters, 2017, 110, . | 3.3 | 5 |
| 104 | Importance of point defect reactions for the atomic-scale roughness of IIIâ€“V nanowire sidewalls. Nanotechnology, 2019, 30, 324002. | 2.6 | 5 |
| 105 | Influence of surface band bending on a narrow band gap semiconductor: Tunneling atomic force studies of graphite with Bernal and rhombohedral stacking orders. Physical Review Materials, 2021, 5, . | 2.4 | 5 |
| 106 | Dislocation reaction on p-doped GaAs (011) observed by scanning tunnelling microscopy. Ultramicroscopy, 1992, 42-44, 776-780. | 1.9 | 4 |
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| 108 | Scanning Tunneling Spectroscopy of Ag Films: The Effect of Periodic versus Quasiperiodic Modulation. Physical Review Letters, 2006, 97, 206102. | 7.8 | 4 |

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| 109 | Tracking the subsurface path of dislocations in GaN using scanning tunneling microscopy. Journal of Applied Physics, 2015, 118, 035302. | 2.5 | 4 |
| 110 | Strain and compositional fluctuations in Al0.81In0.19N/GaN heterostructures. Applied Physics Letters, 2016, 109, 132102. | 3.3 | 4 |
| 111 | Formation ofVPâˆ’Zncomplexes in bulk InP(Zn) by migration of P vacancies from the (110) surface. Physical Review B, 2006, 73, . | 3.2 | 3 |
| 112 | Catalystlike behavior of Si adatoms in the growth of monolayer Al film on Si(111). Journal of Chemical Physics, 2010, 133, 014704. | 3.0 | 3 |
| 113 | Electronically Nonalloyed State of a Statistical Single Atomic Layer Semiconductor Alloy. Nano Letters, 2012, 12, 5845-5849. | 9.1 | 3 |
| 114 | Valence band structure and effective masses of GaN(101Â¯0). Physical Review B, 2019, 99, . | 3.2 | 3 |
| 115 | Interplay of anomalous strain relaxation and minimization of polarization changes at nitride semiconductor heterointerfaces. Physical Review B, 2020, 102, . | 3.2 | 3 |
| 116 | Point defects, dopant atoms, and compensation effects in CdSe and CdS cleavage surfaces. Thin Solid Films, 1999, 343-344, 537-540. | 1.8 | 2 |
| 117 | Incorporation of dopant atoms and defects in semiconductors: a microscopic view. Physica B: Condensed Matter, 2003, 340-342, 1159-1165. | 2.7 | 2 |
| 118 | Spontaneous 2D Accumulation of Charged Be Dopants in GaAspâˆ’nSuperlattices. Physical Review Letters, 2006, 96, 076101. | 7.8 | 2 |
| 119 | Locally probing the screening potential at a metal-semiconductor interface. Physical Review B, 2010, 81, . | 3.2 | 2 |
| 120 | Meandering of overgrown v-shaped defects in epitaxial GaN layers. Applied Physics Letters, 2014, 105, 012105. | 3.3 | 2 |
| 121 | Effective mass of a two-dimensional âˆš3 Ã— âˆš3 Ga single atomic layer on Si(111). Surface Science, 2014, 630, 225-228. | 1.9 | 2 |
| 122 | Resistive switching in optoelectronic III-V materials based on deep traps. Scientific Reports, 2018, 8, 9483. | 3.3 | 2 |
| 123 | Iuliacumite: A Novel Chemical Short-Range Order in a Two-Dimensional Wurtzite Single Monolayer InAs<sub>1â€“x</sub>Sb<sub>x</sub> Shell on InAs Nanowires. Nano Letters, 2019, 19, 8801-8805. | 9.1 | 2 |
| 124 | Interplay of intrinsic and extrinsic states in pinning and passivation of m-plane facets of GaN n-p-n junctions. Journal of Applied Physics, 2020, 128, . | 2.5 | 2 |
| 125 | Atomically-resolved interlayer charge ordering and its interplay with superconductivity in YBa2Cu3O6.81. Nature Communications, 2021, 12, 3893. | 12.8 | 2 |
| 126 | Dislocation bending in GaN/step-graded (Al,Ga)N/AlN buffer layers on Si(111) investigated by STM and STEM. Philosophical Magazine, 2018, 98, 3072-3085. | 1.6 | 1 |

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| 127 | Chemical nature of the anion antisite in dilute phosphide <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>GaA</mml:mi><mml:msub><mml:mi mathvariant="normal">s</mml:mi><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^'</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub><mml:msub><mml:mi mathvariant="normal">P</mml:mi><mml:mi>x</mml:mi></mml:msub></mml:mrow></mml:math> alloy grown at low temperature. Physical Review Materials, 2018, 2, . | 2.4 | 1 |
| 128 | Scanning tunneling microscopy of defects in quasiperiodically ordered surfaces. Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing, 2000, 294-296, 826-829. | 5.6 | 0 |
| 129 | In situ manipulation of scanning tunneling microscope tips without tip holder. Review of Scientific Instruments, 2010, 81, 013706. | 1.3 | 0 |
| 130 | Roughness of electronic interfaces in Ga As p-n multilayers investigated by cross-sectional scanning tunneling microscopy. Materials Research Society Symposia Proceedings, 2002, 719, 1241. | 0.1 | 0 |